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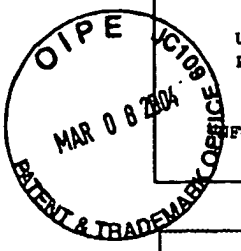

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
WSL	EP 0 951 072 A1	10/1999	European				
	EP 0 933 820 A1	8/1999	European				
	EP 0 924 766 A2	6/1999	European				
	EP 0 920 059 A2	6/1999	European				
	EP 0 869 511 A2	10/1998	European				
	EP 0 860 878 A2	8/1998	European				
	EP 0 858 109 A2	8/1998	European				
	EP 0 844 671 B1	11/2002	European				
	EP 0 836 194 B1	5/2000	European				
	EP 0 788 165 A2	8/1997	European				
	EP 0 744 772 B1	8/2002	European				
	EP 0 739 097 A2	10/1996	European				
	EP 0 731 972 B1	11/2001	European				
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WSL	EP 0 727 820 A1	8/1996	European				
	EP 0 726 601 B1	9/2001	European				
	EP 0 725 402 B1	9/2002	European				
	EP 0 689 252 B1	8/2000	European				
	EP 0 682 370 B1	9/2000	European				
	EP 0 642 173 B1	7/1999	European				
	EP 0 642 173 A1	3/1995	European				
	EP 0 606 758 B1	9/2000	European				
	EP 0 601 590 B1	4/2000	European				
	EP 0 599 506 A1	6/1994	European				
	EP 0 599 388 B1	8/2000	European				
	EP 0 579 566 A2	1/1994	European				
	EP 0 564 204 A2	10/1993	European				
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WSL	EP 0 510 607 B1	2/1998	European				
	EP 0 465 961 B1	8/1995	European				
	EP 0 366 882 B1	5/1995	European				
	EP 0 362 961 B1	2/1994	European				
	EP 0 359 551 B1	12/1994	European				
	EP 0 354 348 A2	2/1990	European				
	EP 0 350 057 B1	1/1990	European				
	EP 0 333 426 B1	7/1996	European				
	EP 0 300 157 B1	5/1993	European				
	EP 0 253 631 B1	4/1992	European				
	EP 0 245 515 B1	4/1997	European				
	EP 0 207 619 B1	8/1991	European				
	EP 0 202 515 B1	3/1991	European				
	EP 0 175 378 B1	11/1991	European				

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WSL	2002/0036322	3/2002	Divakauni et al.			
	5,446,299	8/1995	Acovic et al.			
	5,568,356	10/1996	Schwartz			
	5,627,092	5/1997	Alsmeier et al.			
	5,631,186	5/1997	Park et al.			
	5,740,099	4/1998	Tanigawa			
	5,877,978	3/1999	Morishita et al.			
	5,930,648	7/1999	Yang			
	5,939,745	8/1999	Park et al.			
	5,943,258	8/1999	Houston et al.			
	5,968,840	10/1999	Park et al.			
	5,977,578	11/1999	Tang			
	6,018,172	1/2000	Hidada et al.			

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
WSL	6,297,090	10/2001	Kim			
↓	6,384,445	5/2002	Hidaka et al.			
↓	6,590,258	7/2003	Divakauni et al.			

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO	
WSL	JP 62 272561	11/1987	Japanese				
↓	JP 8 274277	10/1996	Japanese				
↓	JP 9 82912	3/1997	Japanese				

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WSL	2002/0064913	5/2002	Adkisson et al.			
	2002/0072155	6/2002	Liu et al.			
	2002/0086463	7/2002	Houston et al.			
	2002/0089038	7/2002	Ning			
	2002/0180069	12/2002	Houston			
	2003/0102497	6/2003	Fried et al.			
	2003/0123279	7/2003	Aipperspach et al.			
	4,791,610	12/1988	Takemae			
	5,388,068	2/1995	Ghoshal et al.			
	5,446,299	8/1995	Acovic et al.			
	5,466,625	11/1995	Hsieh et al.			
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USL	5,778,243	7/1998	Aipperspach et al.			
	5,784,311	7/1998	Assaderaghi et al.			
	5,811,283	9/1998	Sun			
	5,886,376	3/1999	Acovic et al.			
	5,897,351	4/1999	Forbes			
	5,943,258	8/1999	Houston et al.			
	5,943,581	8/1999	Lu et al.			
	5,960,265	9/1999	Acovic et al.			
	6,096,598	8/2000	Furukawa et al.			
	6,097,056	8/2000	Hsu et al.			
	6,157,216	12/2000	Lattimore et al.			
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	6,177,300	1/2001	Houston et al.			
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ajl2	6,214,694	4/2001	Leobandung et al.			
	6,225,158	5/2001	Furukawa et al.			
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	6,552,398	4/2003	Hsu et al.			
	6,556,477	4/2003	Hsu et al.			
	6,566,177	5/2003	Radens et al.			
	6,590,258	7/2003	Divakauni et al.			
	6,590,259	7/2003	Adkisson et al.			

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WSL	JP 11 87649	3/1999	Japanese				

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	6,617,651	9/2003	Ohsawa			
	6,531,754	3/2003	Nagano et al.			
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WSL	2003-243528	8/2003	Japanese				
	2002-94027	3/2002	Japanese				
	2002-176154	6/2002	Japanese				
	2002-246571	8/2002	Japanese				
	2002-329795	11/2002	Japanese				
	2002-343886	11/2002	Japanese				
	2002-353080	12/2002	Japanese				
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	2003-86712	3/2003	Japanese				

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WSL	DRAM Design Using the Taper-Isolated Dynamic RAM Cell, Leiss et al., IEEE Transactions on Electron Devices, Vol. ED-29, No. 4, April 1982, pp707-714

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WSL	2003-100641	4/2003	Japanese				
	2003-100900	4/2003	Japanese				
	2003-132682	5/2003	Japanese				
	2003-203967	7/2003	Japanese				
	2003-243528	8/2003	Japanese				
	09046688	2/1997	Japanese				
	JP 8-213624	8/1996	Japanese				
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